



SSC8336GQ4

Dual Asymmetric N-Channel Enhancement Mode MOSFET

➤ **Features**

VDS	VGS	RDSON Typ.	ID
30V	±20V	13mR@10V	12A
		17mR@4V5	

➤ **Description**

This device uses advanced trench technology to provide excellent RDSON and low gate charge. This device is suitable for use as a load switch or in PWM applications.

➤ **Applications**

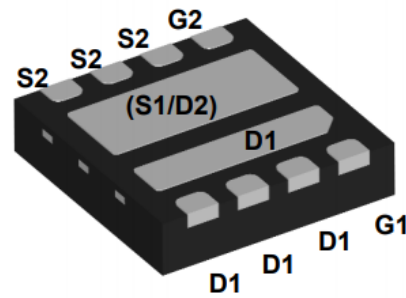
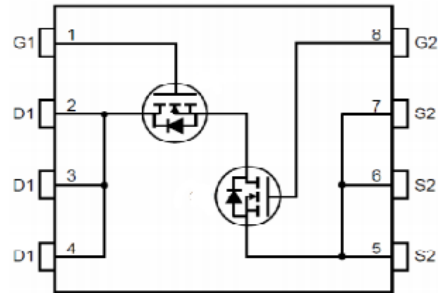
- Power Management in notebook computer
- Portable Equipment
- Battery Powered Systems

➤ **Ordering Information**

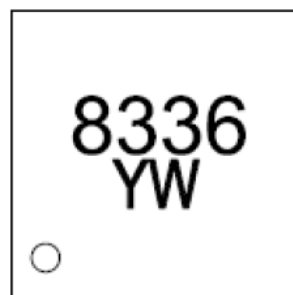
Device	Package	Shipping
SSC8336GQ4	DFN3X3	5000/Reel

➤ **Pin configuration**

Top view



Bottom View



(Y: year/W: week)

Marking



➤ **Absolute Maximum Ratings**($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Unit	
V_{DSS}	Drain-to-Source Voltage	30	V	
V_{GSS}	Gate-to-Source Voltage	± 20	V	
I_D	Continuous Drain Current	$TC=25^{\circ}\text{C}$	12	A
		$TC=100^{\circ}\text{C}$	9	A
I_{DM}	Pulsed Drain Current ^b	36	A	
I_{DSM}	Continuous Drain Current ^a	$TA=25^{\circ}\text{C}$	10	A
		$TA=70^{\circ}\text{C}$	8	A
P_D	Power Dissipation ^c	$TC=25^{\circ}\text{C}$	20	W
		$TC=100^{\circ}\text{C}$	8	W
P_{DSM}	Power Dissipation ^a	$TA=25^{\circ}\text{C}$	2.5	W
		$TA=70^{\circ}\text{C}$	0.9	W
I_{AS}	Avalanche Current	20	A	
E_{AS}	Avalanche Energy, $L=0.1\text{mH}$	20	mJ	
T_J	Operation junction temperature	-55 to 150	$^{\circ}\text{C}$	
T_{STG}	Storage temperature range	-55 to 150	$^{\circ}\text{C}$	

➤ **Thermal Resistance Ratings**($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Typical	Maximum	Unit
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance ^a		55	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}$	Junction-to-Case Thermal Resistance		6.5	

Note:

- a. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz.copper,in a still air environment with $T_A=25^{\circ}\text{C}$.The value in any given application depends on the user is specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.
- b. Repetitive rating, pulse width limited by junction temperature.
- c. The power dissipation P_D is based on $T_J(\text{MAX})=150^{\circ}\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.

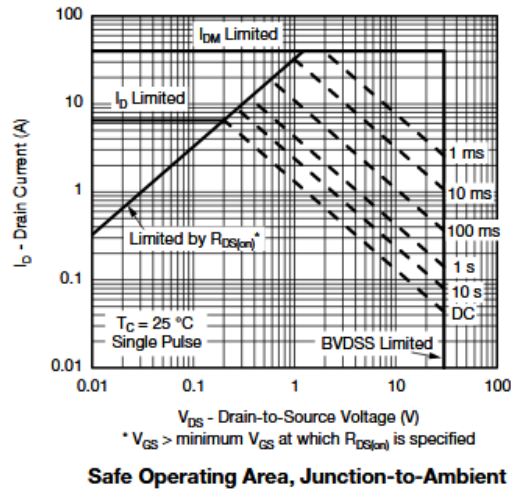
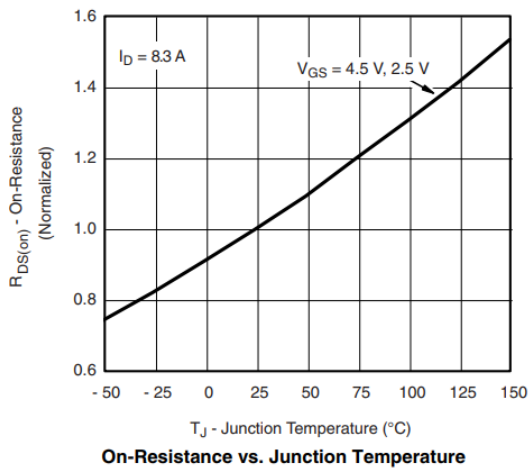
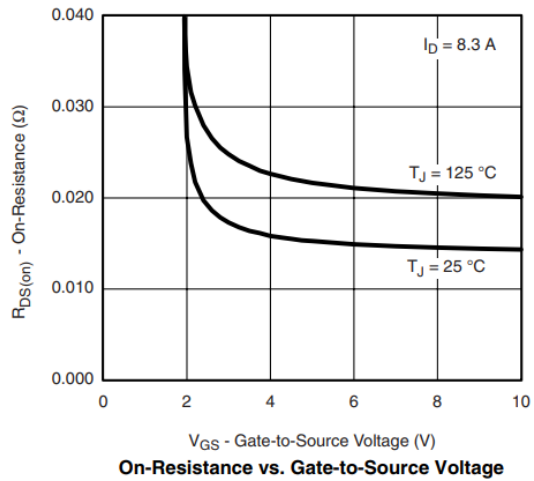
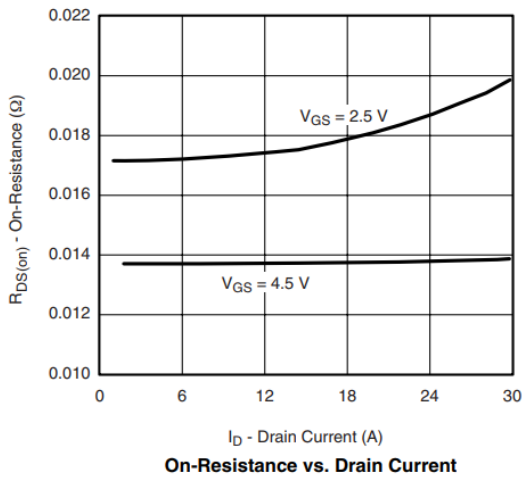
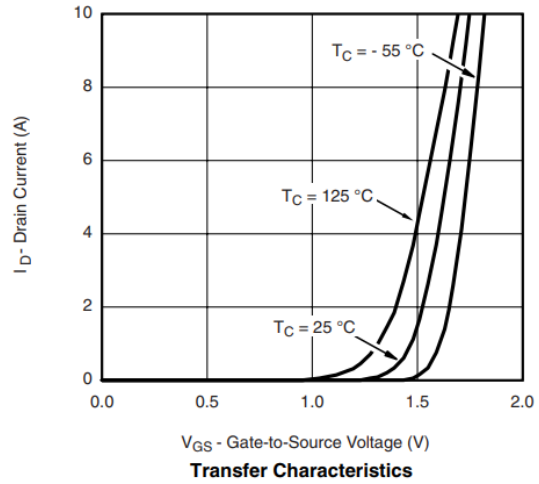
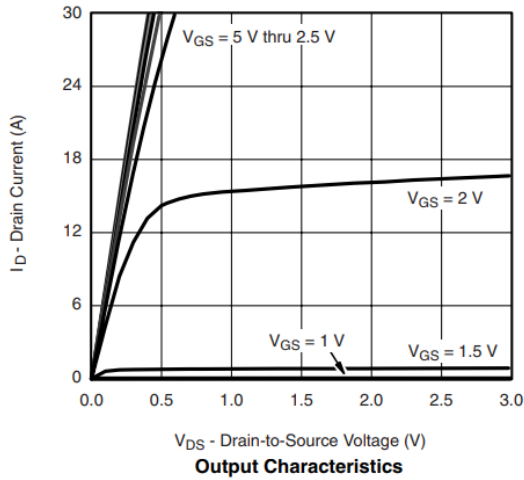


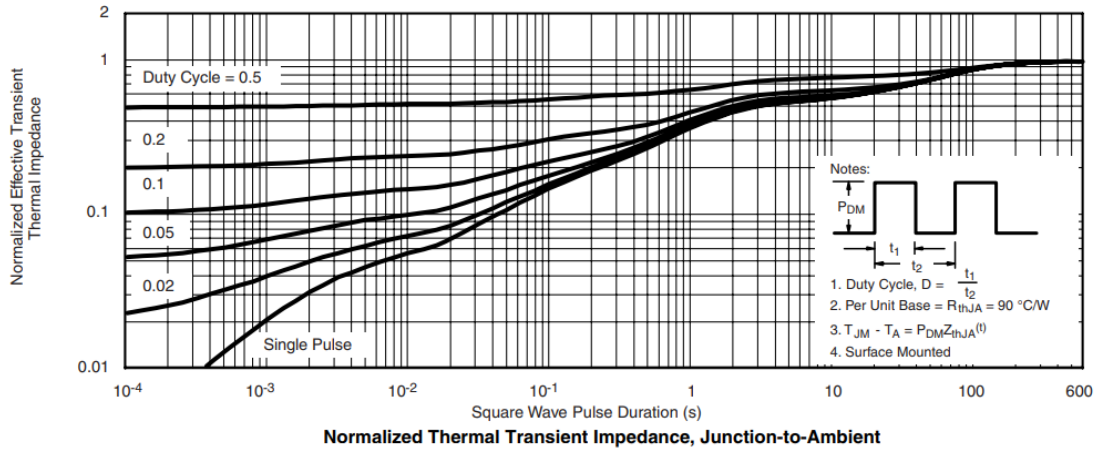
➤ **Electronics Characteristics**($T_A=25^{\circ}\text{C}$ unless otherwise noted)

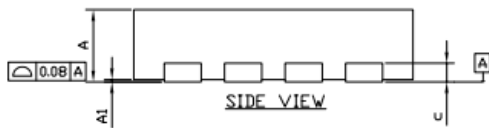
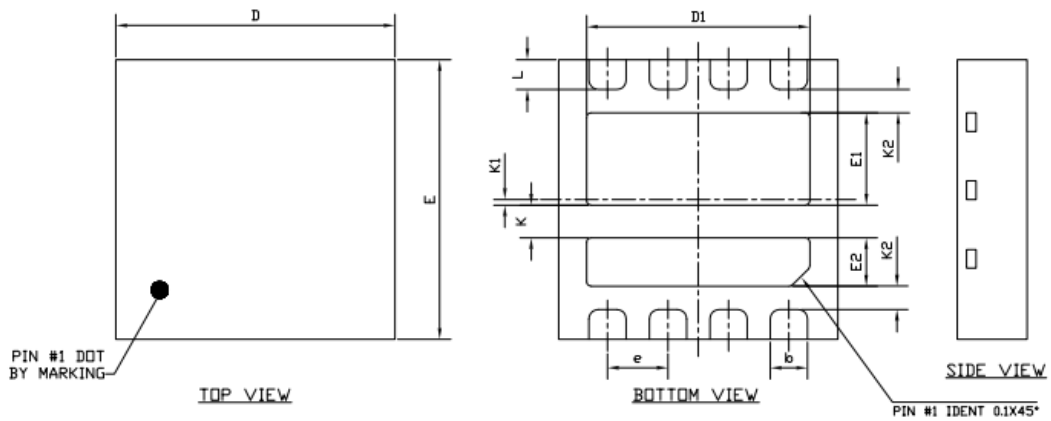
Symbol	Parameter	Test Conditions	Min	Typ.	Max	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.1	1.7	2.1	V
$R_{DS(on)}$	Drain-Source On- Resistance	$V_{GS}=10V, I_D=9A$		13	18	mR
		$V_{GS}=4.5V, I_D=7.5A$		17	24	
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=24V, V_{GS}=0V$			1	μA
I_{GSS}	Gate-Source leak current	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
V_{SD}	Forward Voltage	$V_{GS}=0V, I_S=0.5A$		0.8	1.3	V
G_{FS}	Transconductance	$V_{DS}=15V, I_D=10A$		20		S
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1MHz$		530		pF
C_{oss}	Output Capacitance			200		
C_{rss}	Reverse Transfer Capacitance			105		
$T_{D(ON)}$	Turn-on delay time			14		
T_r	Rise time	$V_{GS}=10V,$ $V_{DS}=15V, R_G=3R, R_L=2.3R$		11		ns
$T_{D(OFF)}$	Turn-off delay time			15		
T_f	Fall time			8		
Q_g	Total Gate charge			17		
Q_{gs}	Gate to Source charge	$V_{GS}=10V, V_{DS}=15V, I_D=13A$		2.7		nC
Q_{gd}	Gate to Drain charge			3.7		



➤ **Typical Characteristics** ($T_A=25^\circ\text{C}$ unless otherwise noted)





➤ Package Information

DFN3X3

SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.75	0.80	0.028	0.030	0.032
A1	0.00	---	0.05	0.000	---	0.002
c	0.203 REF.			0.008 REF.		
b	0.35	0.40	0.45	0.014	0.016	0.018
D	2.90	3.00	3.10	0.114	0.118	0.122
D1	2.30	2.40	2.50	0.090	0.094	0.098
E	2.90	3.00	3.10	0.114	0.118	0.122
E1	0.89	0.99	1.09	0.035	0.039	0.043
E2	0.42	0.52	0.62	0.016	0.020	0.024
e	0.65 BSC			0.026 BSC		
L	0.27	0.32	0.37	0.011	0.013	0.015
K	0.35 REF.			0.014 REF.		
K1	0.06 REF.			0.002 REF.		
K2	0.25 REF.			0.010 REF.		



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